

ABSTRACT OF THE DISCLOSURE

A semiconductor apparatus includes a substrate,
a buffer layer made of a monocrystal semiconductor
material and formed on the substrate, a strained-Si
5 layer formed on the buffer layer and having a lattice
constant different from that of the buffer layer, a
monocrystal insulating film formed on the strained-Si
layer and made of a material having a rare earth
structure with a lattice constant different from that
10 of Si, and an electrode formed on the insulating film.